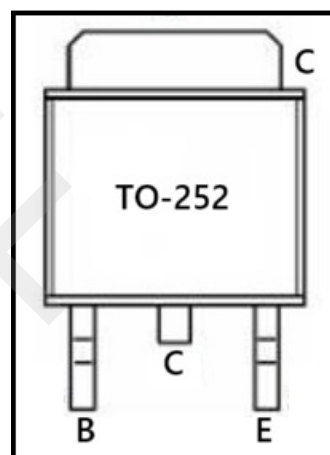


MJD42C

- Complementary to: MJD41C
- Package: TO-252

Maximum Ratings (Ta = 25°)

Parameter	Symbol	Rating	Unit
Collector-base voltage	BV_{CBO}	-100	V
Collector-emitter voltage	BV_{CEO}	-100	V
Emitter-base voltage	BV_{EBO}	-5	V
Collector current	I_{CM}	-6	A
Collector Power Dissipation	P_C	1.25	W
	$P_C(T_C=25^\circ)$	20	
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55~+150	°C



Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=-1mA, I_E=0$	-100			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=-30mA, I_B=0$	-100			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=-1mA, I_C=0$	-5			V
collector-emitter cut-off current	I_{CEO}	$V_{CE}=-60V, I_B=0$			-50	μA
emitter-base cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-0.5	mA
DC current gain	H_{FE1}	$V_{CE}=-4V, I_C=-3A$	15		75	
	H_{FE2}	$V_{CE}=-4V, I_C=-0.3A$	30			
collector-emitter saturation voltage	V_{CESAT}	$I_C=-6A, I_B=-0.6A$			-1.5	V
Base-Emitter Saturation Voltage	$V_{BE(ON)}$	$V_{CE}=-4V, I_C=-6A$			-2.0	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-500mA$	3			MHz